

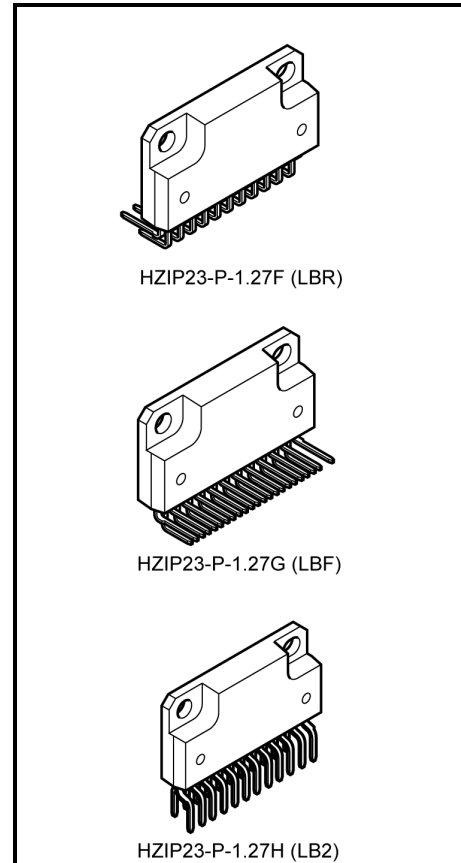
TPD4103AK

The TPD4103AK is a DC brushless motor driver using high voltage PWM control. It is fabricated by high voltage SOI process. The device contains a level shift high-side driver, low-side driver, IGBT outputs, FRDs, and under voltage protection circuits, and thermal shutdown circuits. It is easy to control a DC brushless motor by logic inputs from an MPU or motor controller to the TPD4103AK.

Features

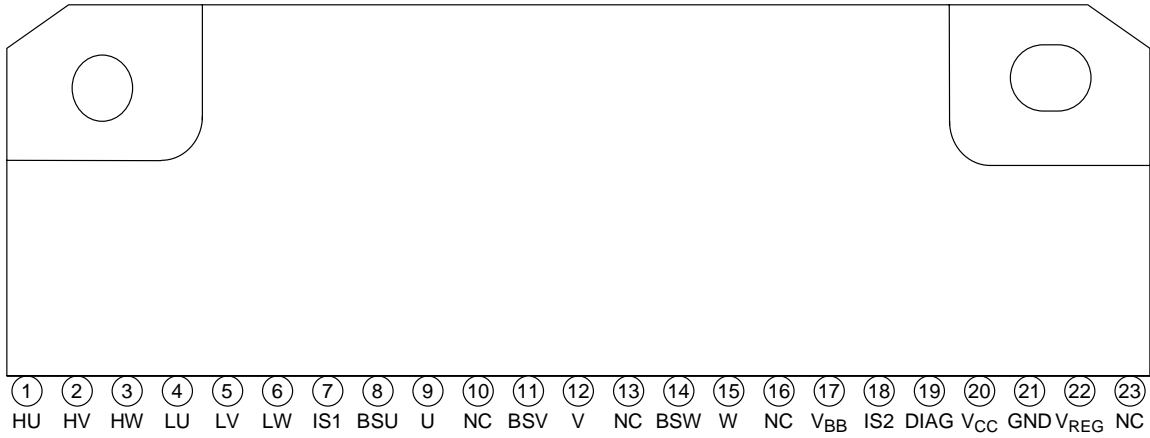
- Bootstrap circuit gives simple high side power supply.
- Bootstrap diodes are built in.
- Dead time can be set to a minimum of 1.4 μ s, which is particularly suited to sine wave drive applications.
- 3-phase bridge output using IGBTs.
- FRDs are built in.
- Includes under voltage protection and thermal shutdown.
- Built-in 7 V (typ.) regulator
- Package: 23-pin HZIP.

This product has a MOS structure and is sensitive to electrostatic discharge. When handling this product, ensure that the environment is protected against electrostatic discharge.

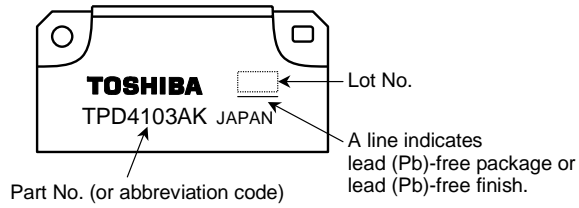


Weight
 HZIP23-P-1.27F : 6.1 g (typ.)
 HZIP23-P-1.27G : 6.1 g (typ.)
 HZIP23-P-1.27H : 6.1 g (typ.)

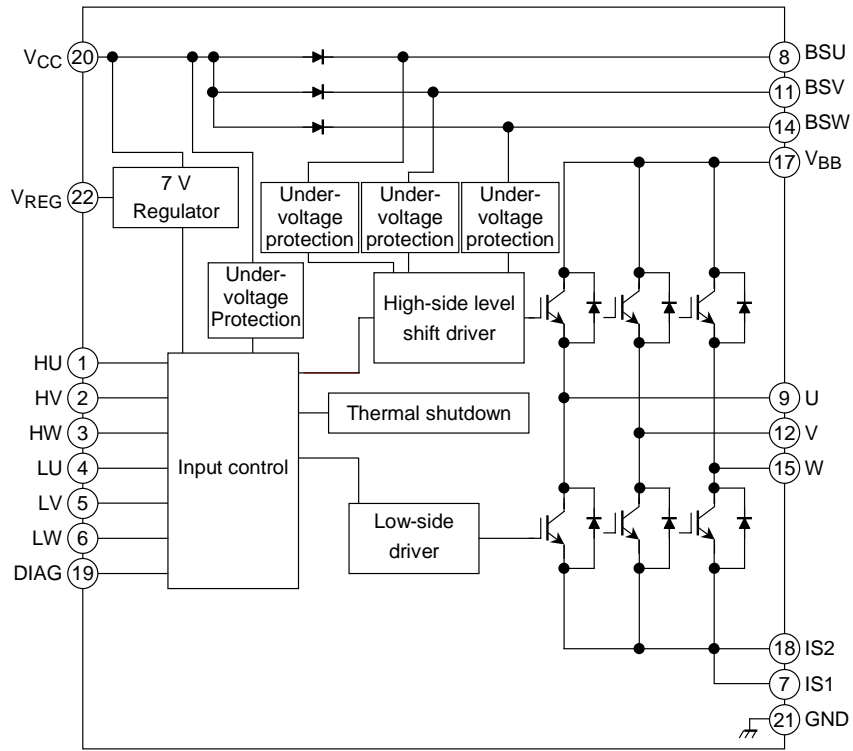
Pin Assignment



Marking



Block Diagram

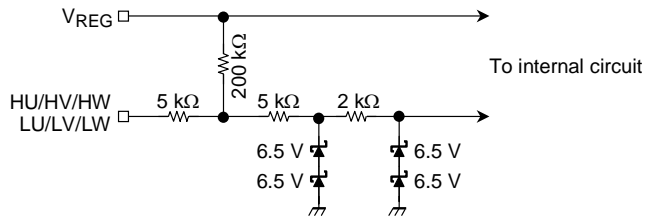


Pin Description

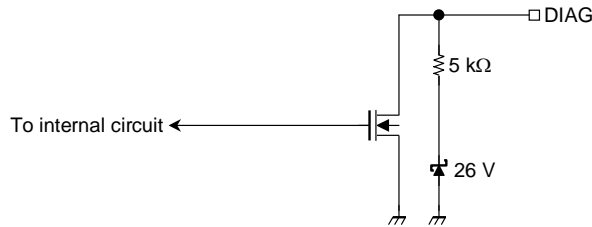
Pin No.	Symbol	Pin Description
1	HU	Control pin of the U-phase high-side IGBT: ON with 1.5V or less; OFF with 3.5V or more
2	HV	Control pin of the V-phase high-side IGBT: ON with 1.5V or less; OFF with 3.5V or more
3	HW	Control pin of the W-phase high-side IGBT: ON with 1.5V or less; OFF with 3.5V or more
4	LU	Control pin of the U-phase low-side IGBT: ON with 1.5V or less; OFF with 3.5V or more
5	LV	Control pin of the V-phase low-side IGBT: ON with 1.5V or less; OFF with 3.5V or more
6	LW	Control pin of the W-phase low-side IGBT: ON with 1.5V or less; OFF with 3.5V or more
7	IS1	IGBT emitter and FRD anode pin.
8	BSU	U-phase bootstrap capacitor connecting pin.
9	U	U-phase output pin.
10	NC	Unused pin, which is not connected to the chip internally.
11	BSV	V-phase bootstrap capacitor connecting pin.
12	V	V-phase output pin.
13	NC	Unused pin, which is not connected to the chip internally.
14	BSW	W-phase bootstrap capacitor connecting pin.
15	W	W-phase output pin.
16	NC	Unused pin, which is not connected to the chip internally.
17	V _{BB}	High-voltage power supply input pin.
18	IS2	IGBT emitter and FRD anode pin.
19	DIAG	With the diagnostic output terminal of open drain , a pull-up is carried out by resistance. It turns it on at the time of unusual.
20	V _{CC}	Control power supply pin. (15V typ.)
21	GND	Ground pin.
22	V _{REG}	7V regulator output pin.
23	NC	Unused pin, which is not connected to the chip internally.

Equivalent Circuit of Input Pins

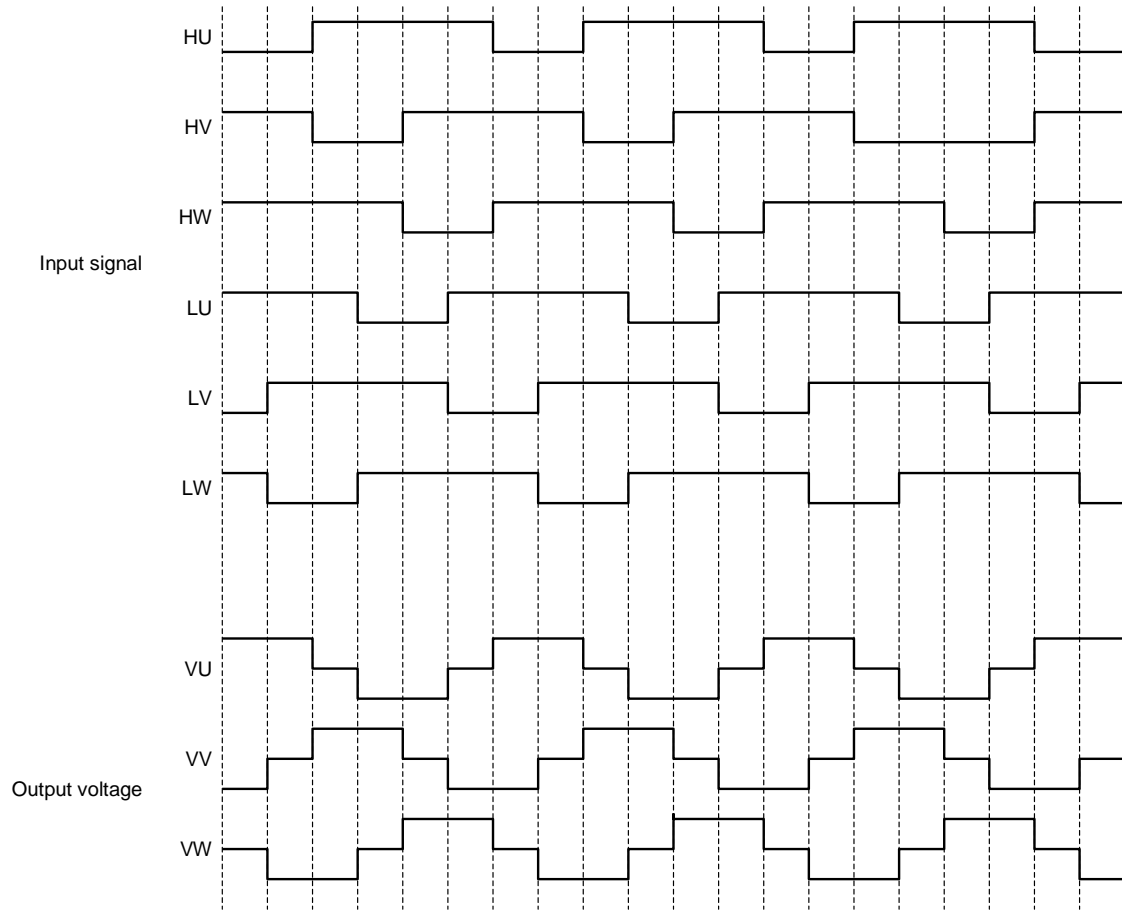
Internal circuit diagram of HU, HV, HW, LU, LV, LW input pins



Internal circuit diagram of DIAG pin



Timing Chart



Truth Table

Mode	Input						Top arm			Bottom arm			DIAG
	HU	HV	HW	LU	LV	LW	U phase	V phase	W phase	U phase	V phase	W phase	
Normal	L	H	H	H	L	H	ON	OFF	OFF	OFF	ON	OFF	OFF
	L	H	H	H	H	L	ON	OFF	OFF	OFF	OFF	ON	OFF
	H	L	H	H	H	L	OFF	ON	OFF	OFF	OFF	ON	OFF
	H	L	H	L	H	H	OFF	ON	OFF	ON	OFF	OFF	OFF
	H	H	L	L	H	H	OFF	OFF	ON	ON	OFF	OFF	OFF
	H	H	L	H	L	H	OFF	OFF	ON	OFF	ON	OFF	OFF
Thermal shutdown	L	H	H	H	L	H	OFF	OFF	OFF	OFF	OFF	OFF	ON
	L	H	H	H	H	L	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	L	H	H	H	L	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	L	H	L	H	H	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	H	L	L	H	H	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	H	L	H	L	H	OFF	OFF	OFF	OFF	OFF	OFF	ON
Under voltage	L	H	H	H	L	H	OFF	OFF	OFF	OFF	OFF	OFF	ON
	L	H	H	H	H	L	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	L	H	H	H	L	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	L	H	L	H	H	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	H	L	L	H	H	OFF	OFF	OFF	OFF	OFF	OFF	ON
	H	H	L	H	L	H	OFF	OFF	OFF	OFF	OFF	OFF	ON

Notes: Release of thermal shutdown protection and under voltage protection depends on release of a self-reset .

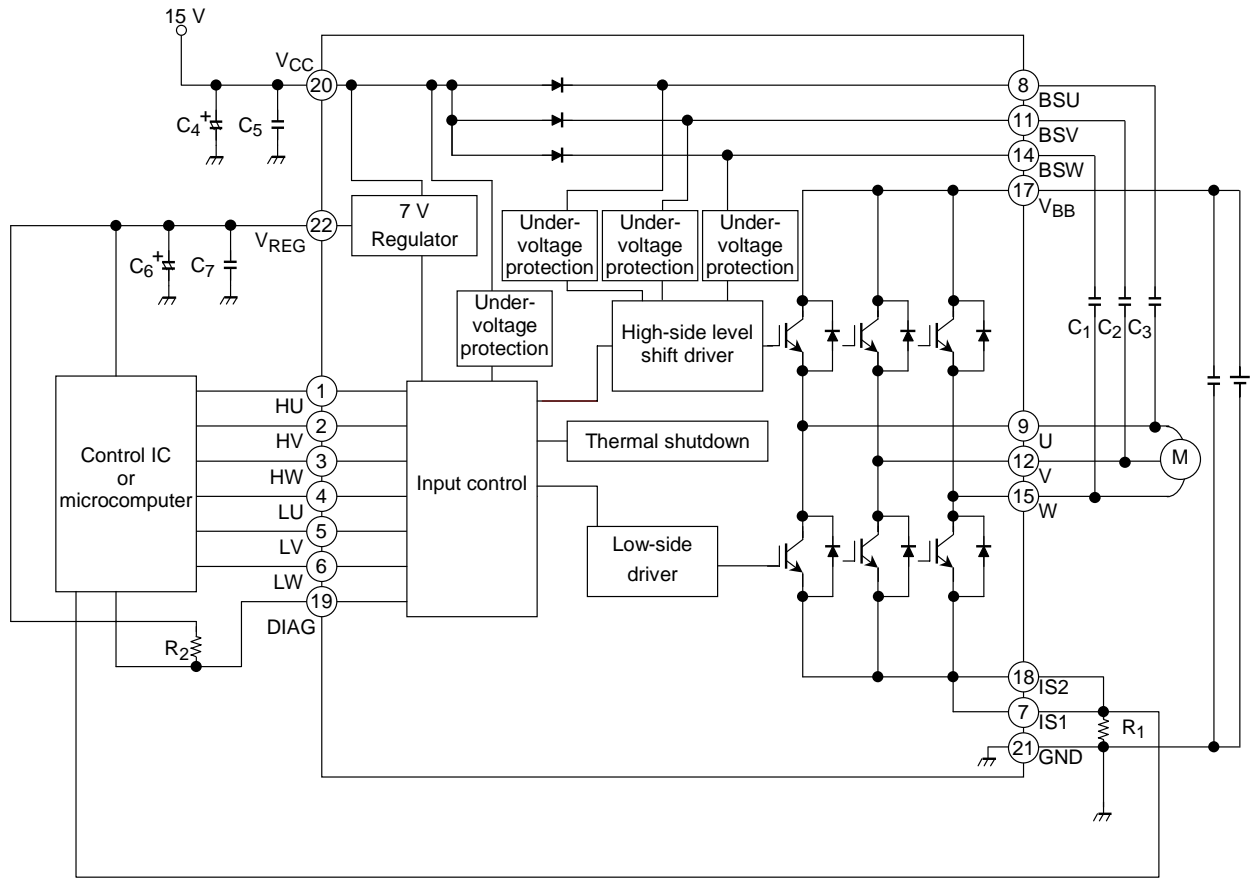
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{BB}	500	V
	V _{CC}	18	V
Output current (DC)	I _{out}	1	A
Output current (pulse)	I _{out}	2	A
Input voltage	V _{IN}	-0.5~7	V
V _{REG} current	I _{REG}	50	mA
Power dissipation (Ta = 25°C)	P _C	4	W
Power dissipation (Tc = 25°C)	P _C	20	W
Operating temperature	T _{jopr}	-20~135	°C
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~150	°C
Lead-heat sink isolation voltage	V _{hs}	1000 (1 min)	V _{rms}

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Operating power supply voltage	V _{BB}	—	50	280	400	V
	V _{CC}	—	13.5	15	16.5	
Current dissipation	I _{BB}	V _{BB} = 400 V	—	0.1	0.5	mA
	I _{CC}	V _{CC} = 15 V	—	1.1	5	
	I _{BS (ON)}	V _{BS} = 15 V, high side ON	—	260	410	μA
	I _{BS (OFF)}	V _{BS} = 15 V, high side OFF	—	230	370	
Input voltage	V _{IH}	V _{IN} = "H"	3.5	—	—	V
	V _{IL}	V _{IN} = "L"	—	—	1.5	
Input current	I _{IH}	V _{IN} = 5 V	—	—	100	μA
	I _{IL}	V _{IN} = 0 V	—	—	150	
Output saturation voltage	V _{CEsatH}	V _{CC} = 15 V, I _C = 0.5 A	—	2.4	3.0	V
	V _{CEsatL}	V _{CC} = 15 V, I _C = 0.5 A	—	2.4	3.0	
FRD forward voltage	V _{FH}	I _F = 0.5 A, high side	—	1.3	2.0	V
	V _{FL}	I _F = 0.5 A, low side	—	1.3	2.0	
Regulator voltage	V _{REG}	V _{CC} = 15 V, I _O = 30 mA	6.5	7	7.5	V
BSD forward voltage	V _{F (BSD)}	I _F = 500 μA	—	0.9	—	V
Thermal shutdown temperature	TSD		150	165	200	°C
Thermal shutdown hysteresis	ΔTSD		—	20	—	°C
V _{CC} under voltage protection	V _{CCUVD}	—	10	11	12	V
V _{CC} under voltage protection recovery	V _{CCUVR}	—	10.5	11.5	12.5	V
V _{BS} under voltage protection	V _{BSUVD}	—	8	9	9.5	V
V _{BS} under voltage protection recovery	V _{BSUVR}	—	8.5	9.5	10.5	V
DIAG saturation voltage	V _{DIAGsat}	I _{DIAG} = 5 mA	—	—	0.5	V
Output on delay time	t _{on}	V _{BB} = 280 V, I _C = 0.5 A	—	1.5	3.0	μs
Output off delay time	t _{off}	V _{BB} = 280 V, I _C = 0.5 A	—	1.2	3.0	μs
Dead time	t _{dead}	V _{BB} = 280 V, I _C = 0.5 A	1.4	—	—	μs
FRD reverse recovery time	t _{rr}	V _{BB} = 280 V, I _C = 0.5 A	—	200	—	ns

Application Circuit Example



External Parts

Standard external parts are shown in the following table.

Part	Recommended Value	Purpose	Remarks
C ₁ , C ₂ , C ₃	25 V/2.2 μF	Bootstrap capacitor	(Note 1)
R ₁	0.62 Ω ± 1% (1 W)	Current detection	(Note 2)
C ₄	25 V/10 μF	V _{CC} power supply stability	(Note 3)
C ₅	25 V/0.1 μF	V _{CC} for surge absorber	(Note 3)
C ₆	16 V/1 μF	V _{REG} power supply stability	(Note 3)
C ₇	16 V/1000 pF	V _{REG} for surge absorber	(Note 3)
R ₃	5.1 kΩ	DIAG pin pull-up resistor	(Note 4)

Note 1: The required bootstrap capacitance value varies according to the motor drive conditions. The capacitor is biased by V_{CC} and must be sufficiently derated for it.

Note 2: The following formula shows the detection current: $I_O = V_R \div R_{IS}$ (For $V_R = 0.5$ V)
Do not exceed a detection current of 1 A when using this product.
(Perform over current protection from the outside.)

Note 3: When using this product, some adjustment is required in accordance with the use environment. When mounting, place as close to the base of the IC leads as possible to improve the ripple and noise elimination.

Note 4: The DIAG pin is open drain. Note that when the DIAG pin is connected to a power supply with a voltage higher than or equal to the V_{CC}, a protection circuit is triggered so that the current flows continuously. If not using the DIAG pin, connect to the GND.

Handling precautions

- (1) Carry out input signal control with a stabilized V_{CC} voltage. (V_{BB} and V_{CC} power may be supplied in either order.)
Note that if the power supply is switched off as described above, this product may be destroyed if the current regeneration route to the V_{BB} power supply is blocked when the V_{BB} line is disconnected by a relay or similar while the motor is still running.
- (2) Application of over voltage such as surge voltage that exceeds the maximum rating may destroy the circuit.

Description of Protection Functions

- (1) Under voltage protection
 This product incorporates the under voltage protection circuit to prevent the IGBT from operating in unsaturated mode when the VCC voltage or the VBS voltage drops.
 When the VCC power supply falls to the IC internal setting ($V_{CCUVD} = 11\text{ V typ.}$), all IGBT outputs shut down regardless of the input. This protection function has hysteresis. When the $V_{CCUVR} (= 11.5\text{ V typ.})$ reaches a level 0.5 V higher than the shutdown voltage, the IC is automatically restored and the IGBT is turned on again by the input signal.
 If the VBS supply voltage drops ($V_{BSUVD} = 9\text{ V typ.}$), the high-side IGBT output shuts down. When the $V_{BSUVR} (= 9.5\text{ V typ.})$ reaches a level 0.5 V higher than the shutdown voltage, the IGBT is turned on again by the input signal.
- (2) Thermal shutdown
 This product incorporates the thermal shutdown circuit to protect itself against the abnormal state when its temperature rises excessively.
 When the temperature of this chip rises due to external causes or internal heat generation, and the internal setting TSD reaches 165°C , all IGBT outputs shut down regardless of the input. This protection function has hysteresis ($\Delta\text{TSD} = 20^{\circ}\text{C typ.}$). When the chip temperature falls to $\text{TSD} - \Delta\text{TSD}$, the chip is automatically restored and the IGBT is turned on again by the input signal.
 Because the chip contains just one temperature detection location, when the chip heats up due to the IGBT, for example, the differences in distance from the detection location in the IGBT (the source of the heat) cause differences in the time taken for shutdown to occur. Therefore, the temperature of the chip may rise higher than the thermal shutdown temperature when the circuit started to operate.

Safe Operating Area

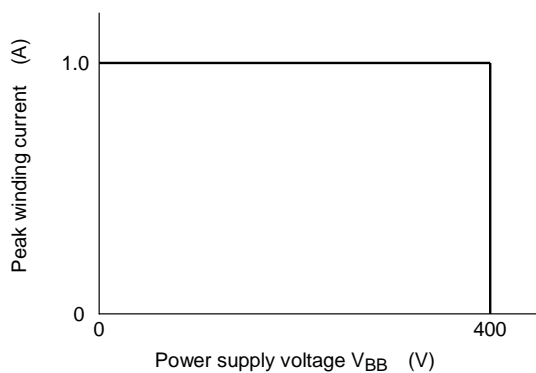


Figure 1 SOA at $T_j = 135^{\circ}\text{C}$

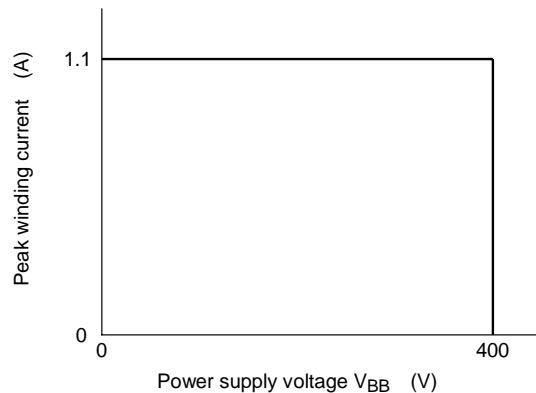
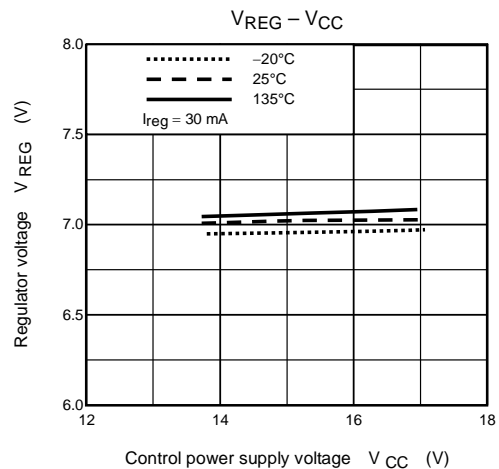
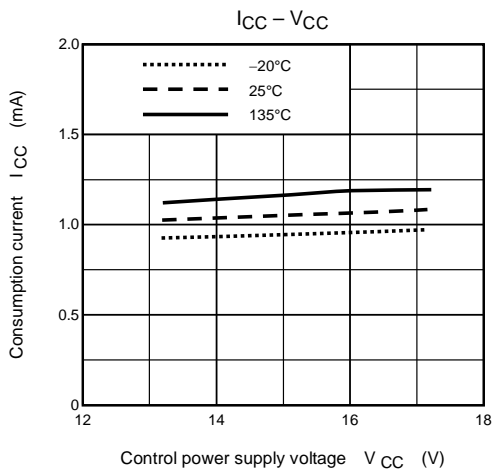
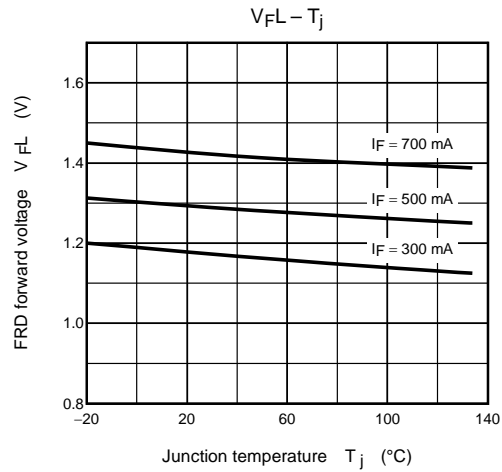
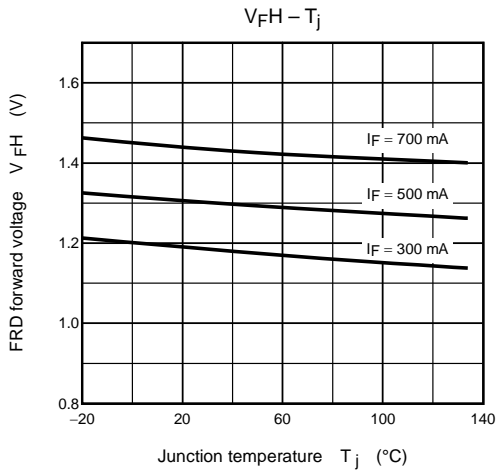
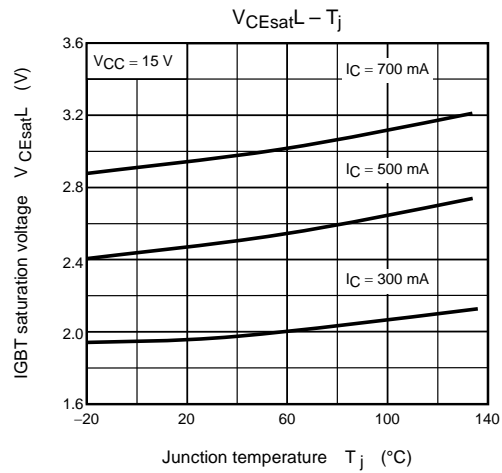
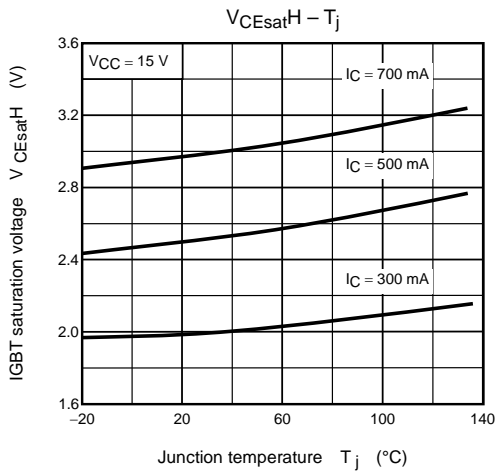
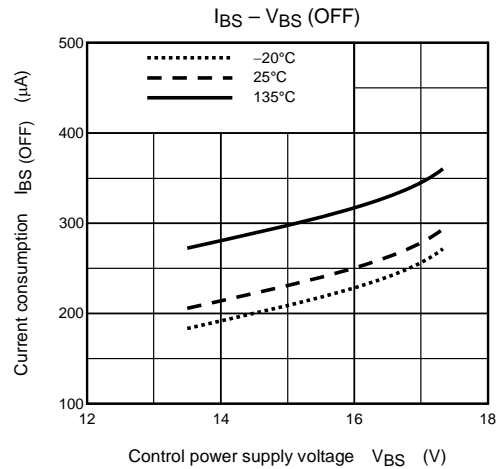
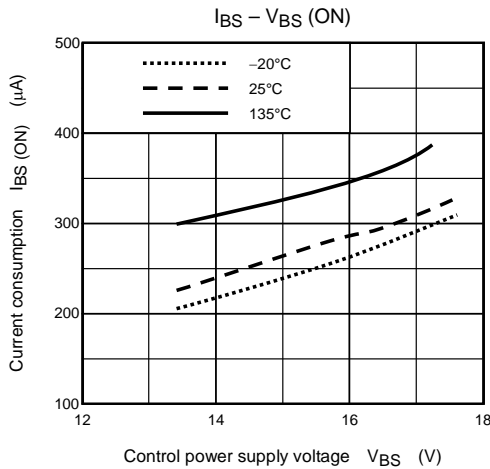
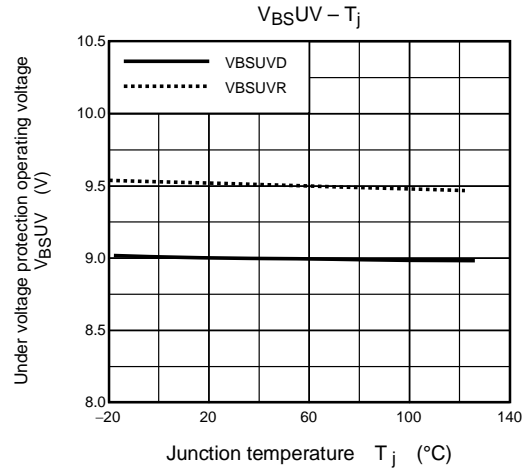
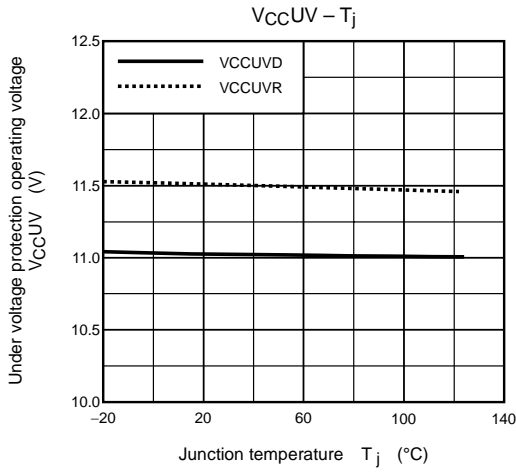
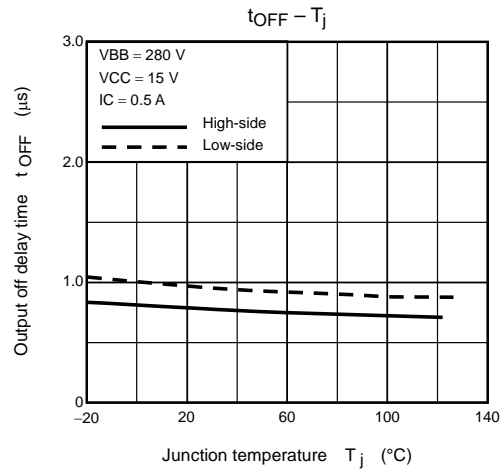
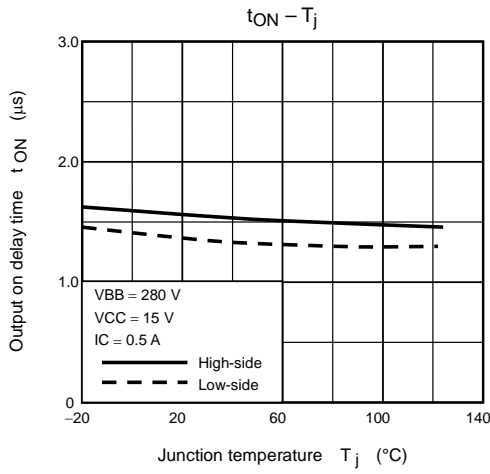
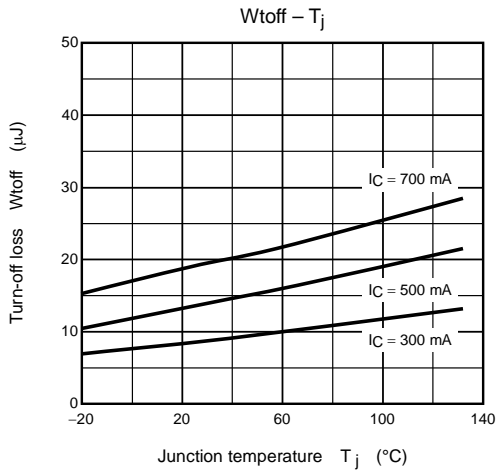
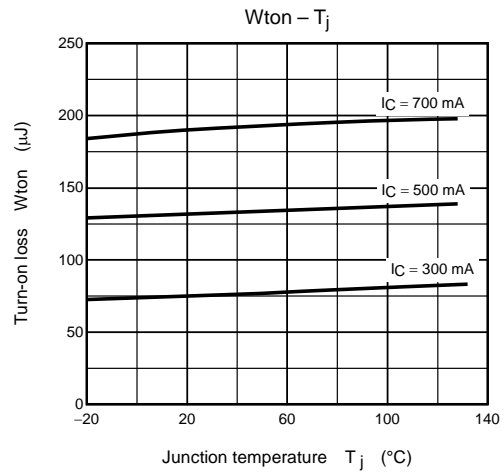
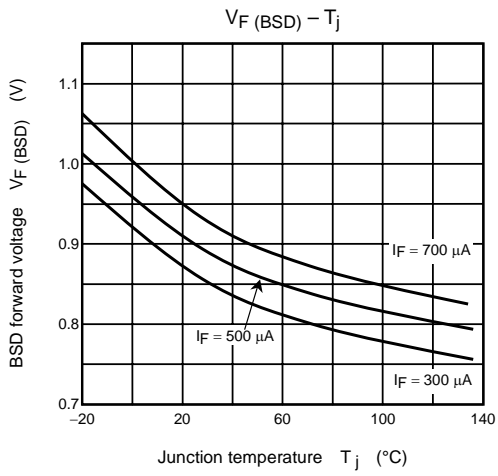


Figure 2 SOA at $T_c = 95^{\circ}\text{C}$

Note 1: The above safe operating areas are $T_j = 135^{\circ}\text{C}$ (Figure 1) and $T_c = 95^{\circ}\text{C}$ (Figure 2). If the temperature exceeds these, the safe operation areas are reduced.

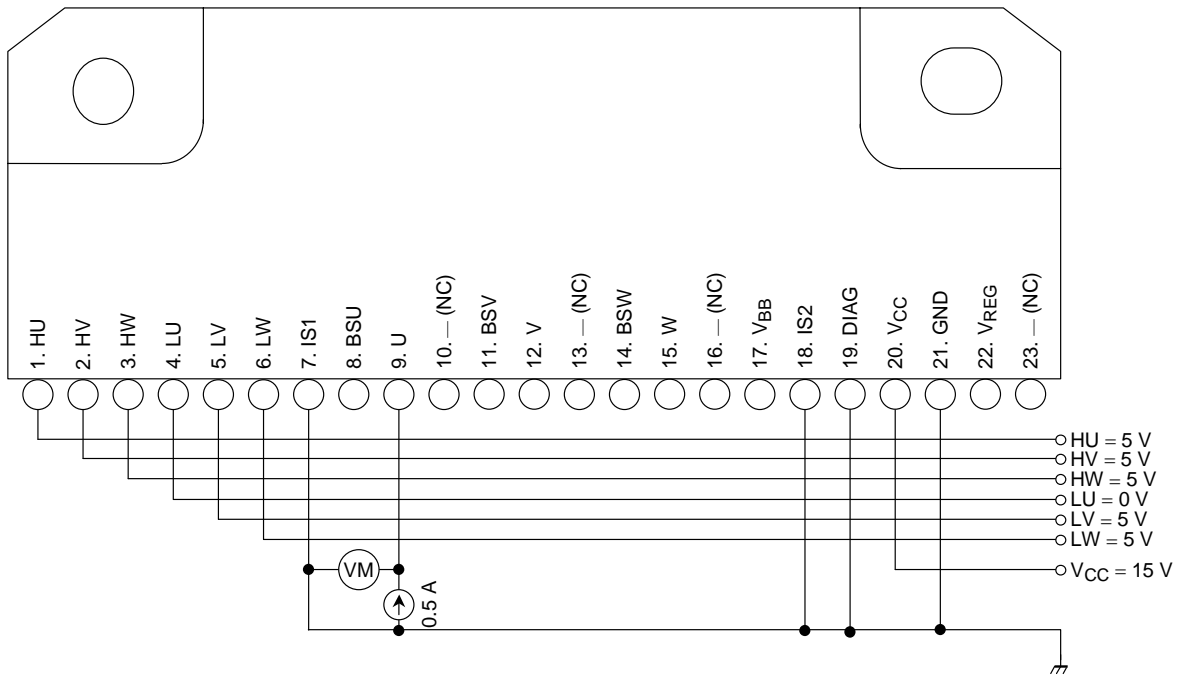




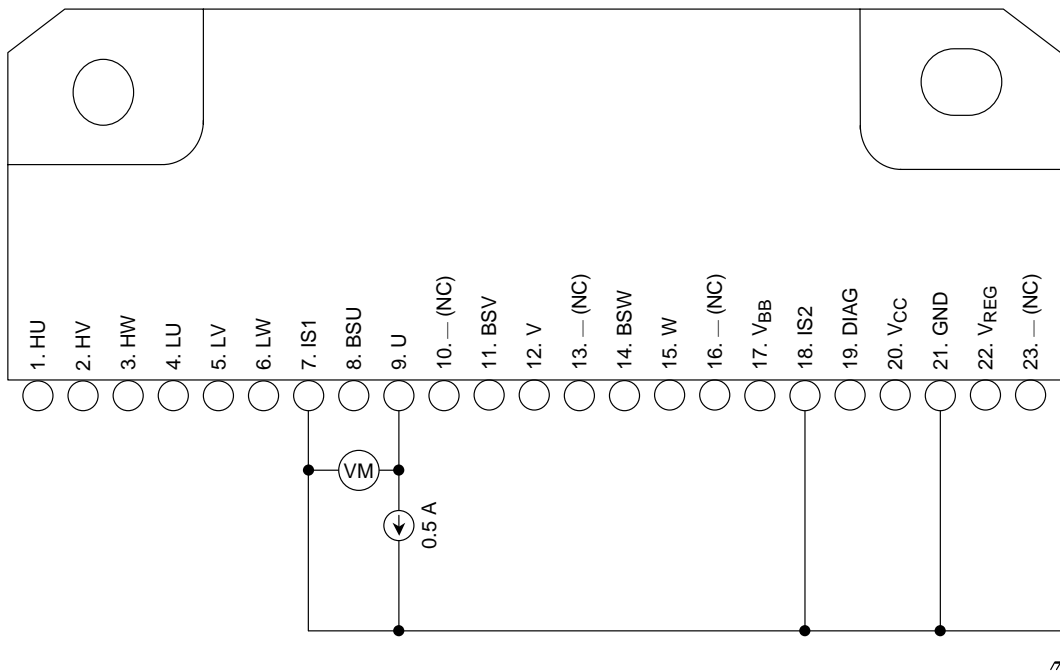


Test Circuits

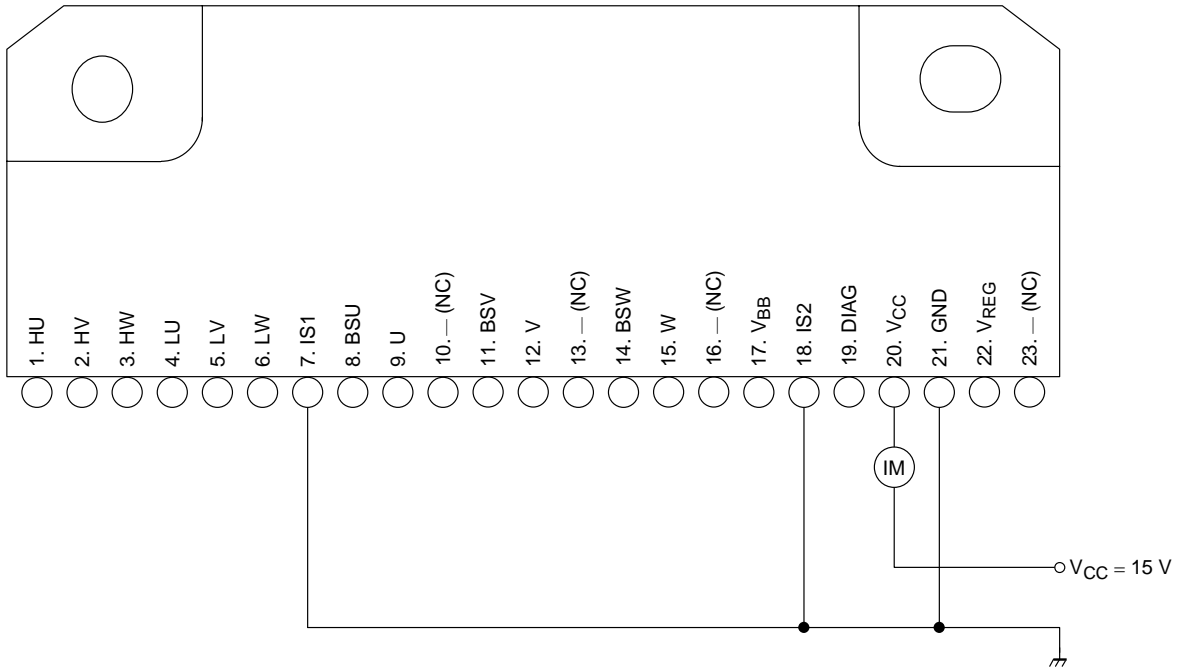
IGBT Saturation Voltage (U-phase low side)



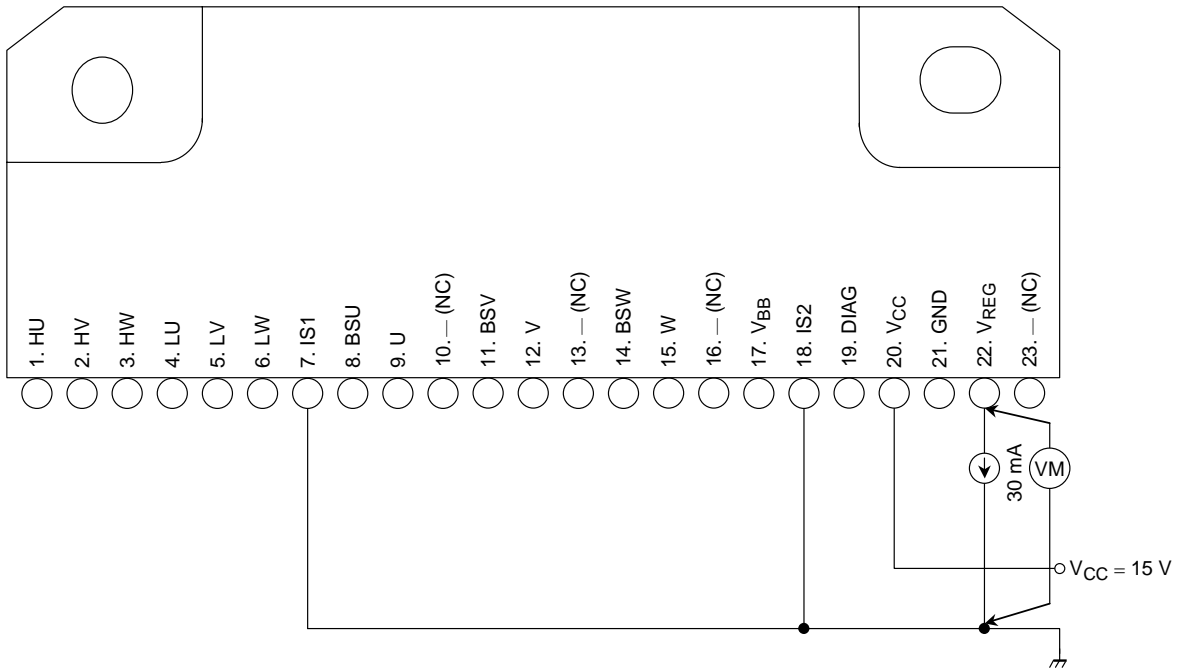
FRD Forward Voltage (U-phase low side)



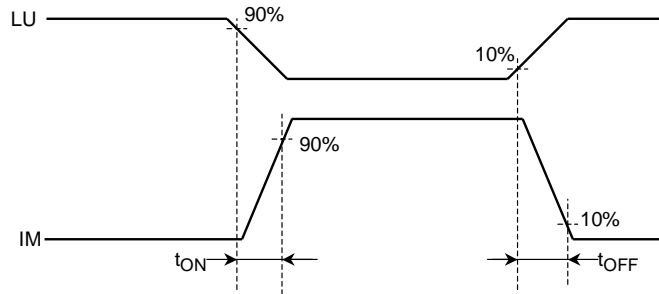
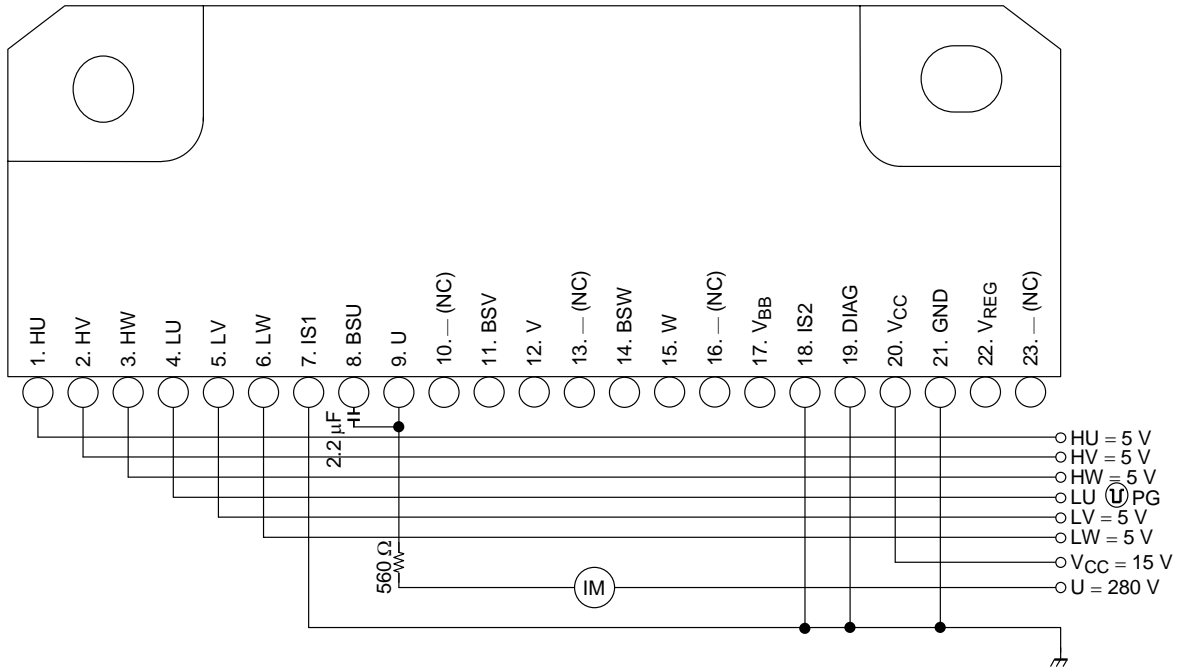
V_{CC} Current Dissipation



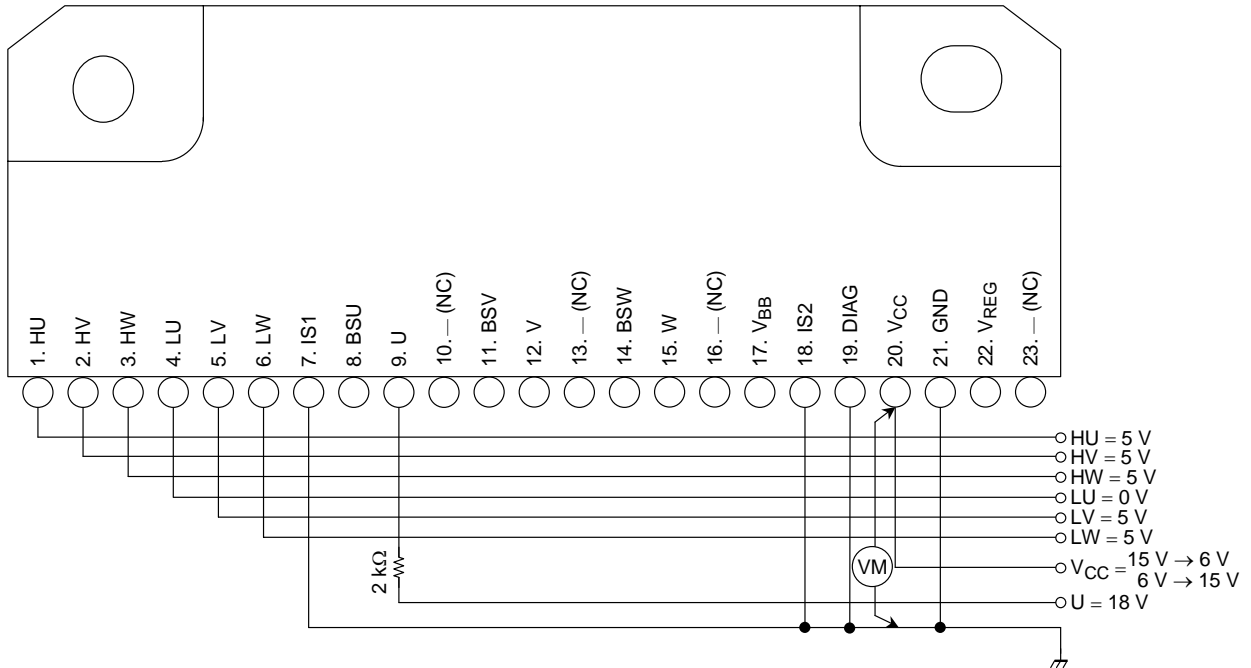
Regulator Voltage



Output ON/OFF Delay Time (U-phase low side)

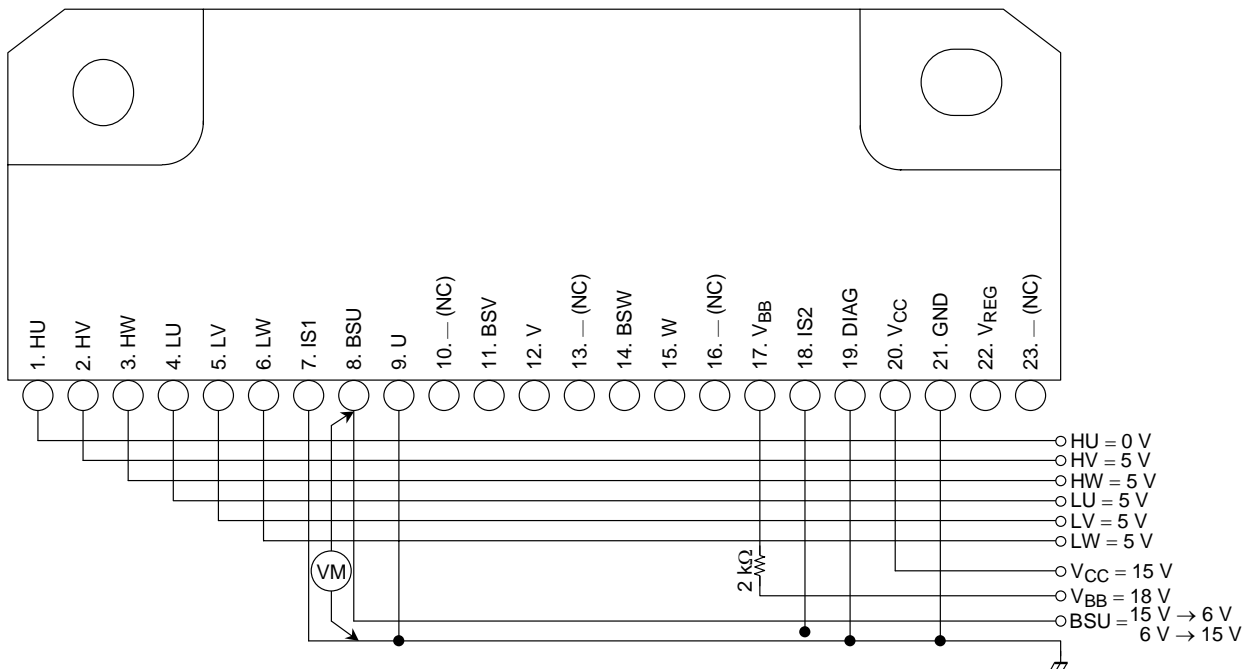


V_{CC} Under Voltage Protection Operation/Recovery Voltage (U-phase low side)



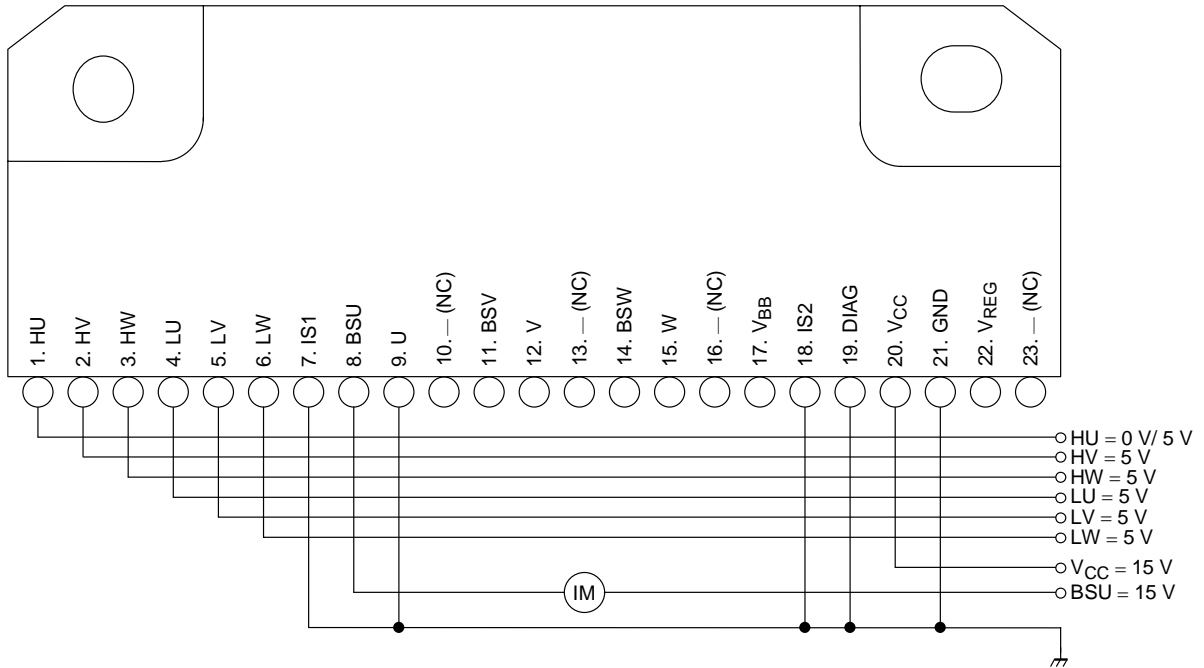
Note: Sweeps the V_{CC} pin voltage from 15 V to decrease and monitors the U pin voltage. The V_{CC} pin voltage when output is off defines the under voltage protection operating voltage. Also sweeps from 6 V to increase. The V_{CC} pin voltage when output is on defines the under voltage protection recovery voltage.

V_{BS} Under Voltage Protection Operation/Recovery Voltage (U-phase high side)

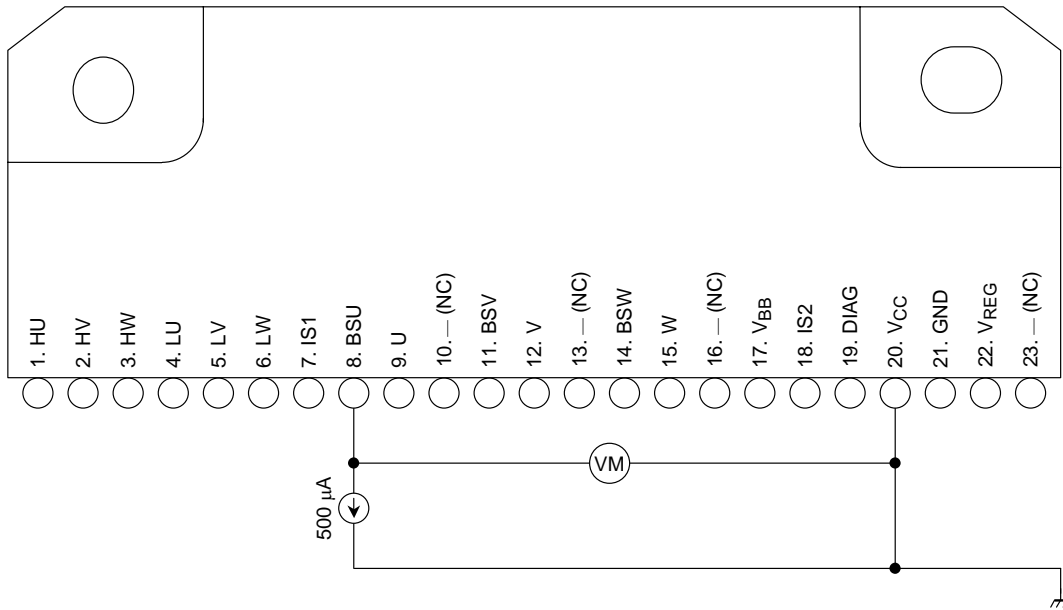


Note: Sweeps the BSU pin voltage from 15 V to decrease and monitors the V_{BB} pin voltage. The BSU pin voltage when output is off defines the under voltage protection operating voltage. Also sweeps the BSU pin voltage from 6 V to increase and change the HU pin voltage at 0 V → 5 V → 0 V. The BSU pin voltage when output is on defines the under voltage protection recovery voltage.

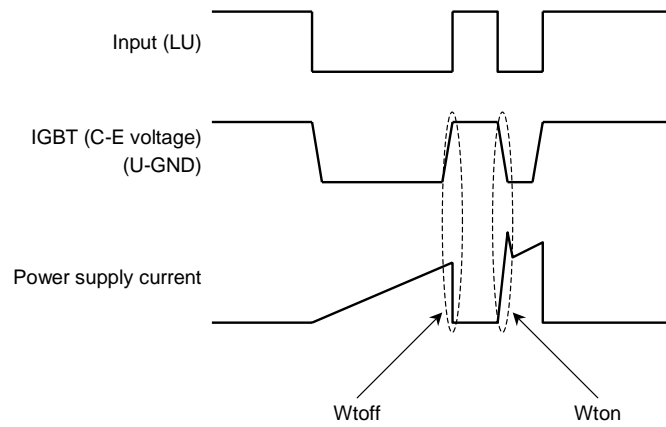
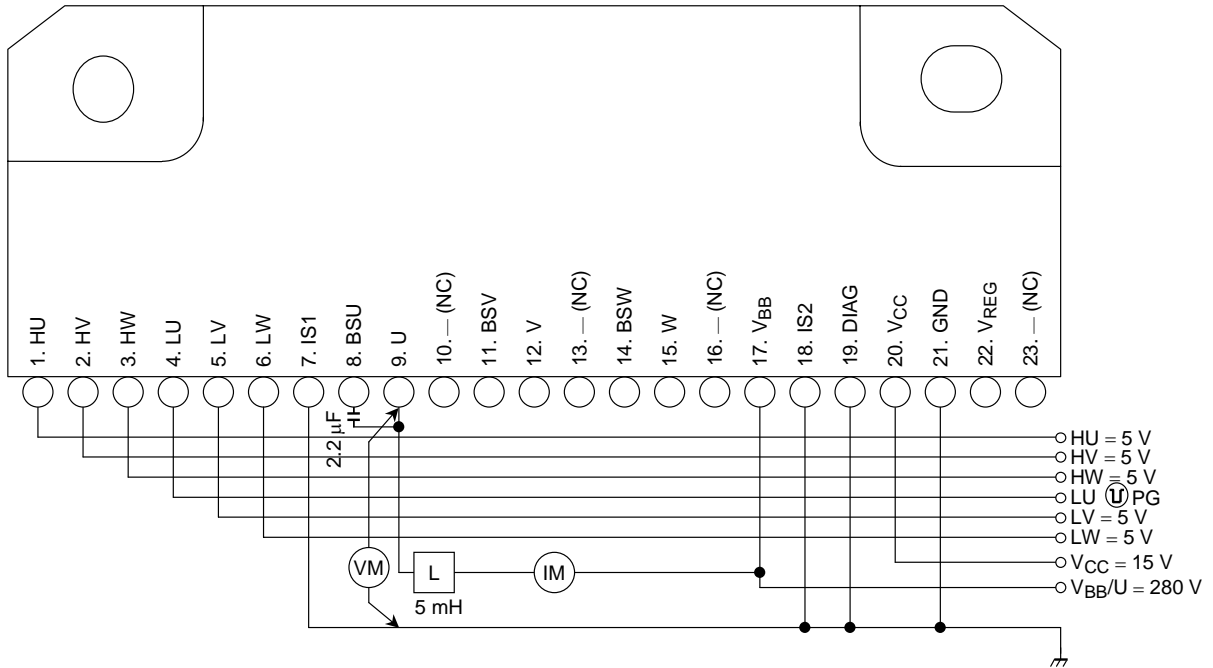
V_{BS} Current Dissipation (U-phase high side)



BSD Forward Voltage (U-phase)



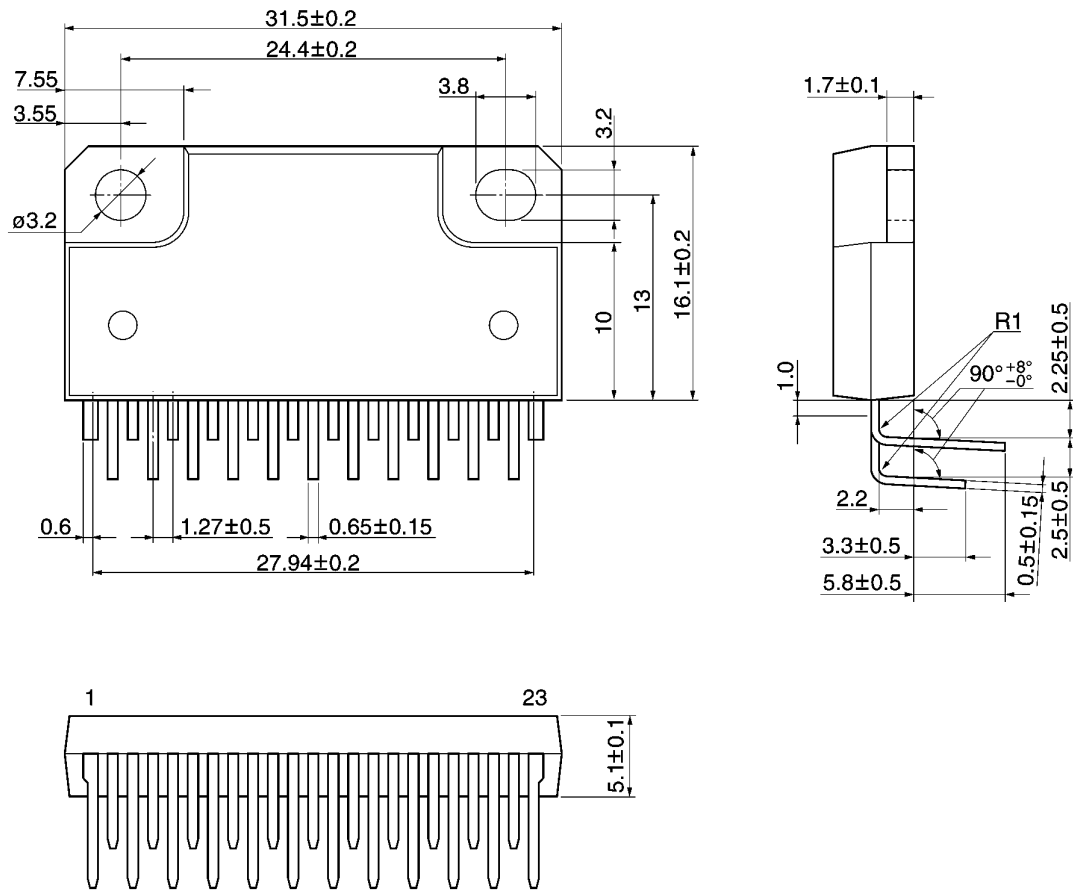
Turn-On/Off SW Loss (low-side IGBT + high-side FRD)



Package Dimensions

HZIP23-P-1.27F

Unit: mm

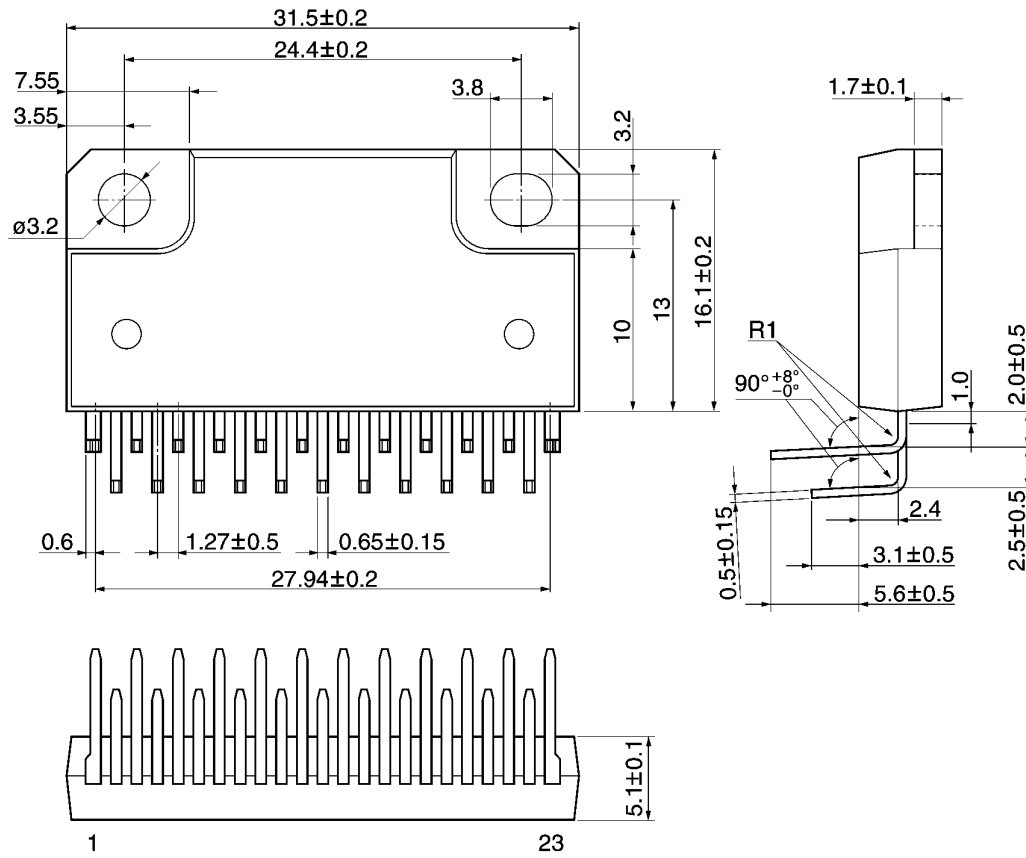


Weight: 6.1 g (typ.)

Package Dimensions

HZIP23-P-1.27G

Unit: mm

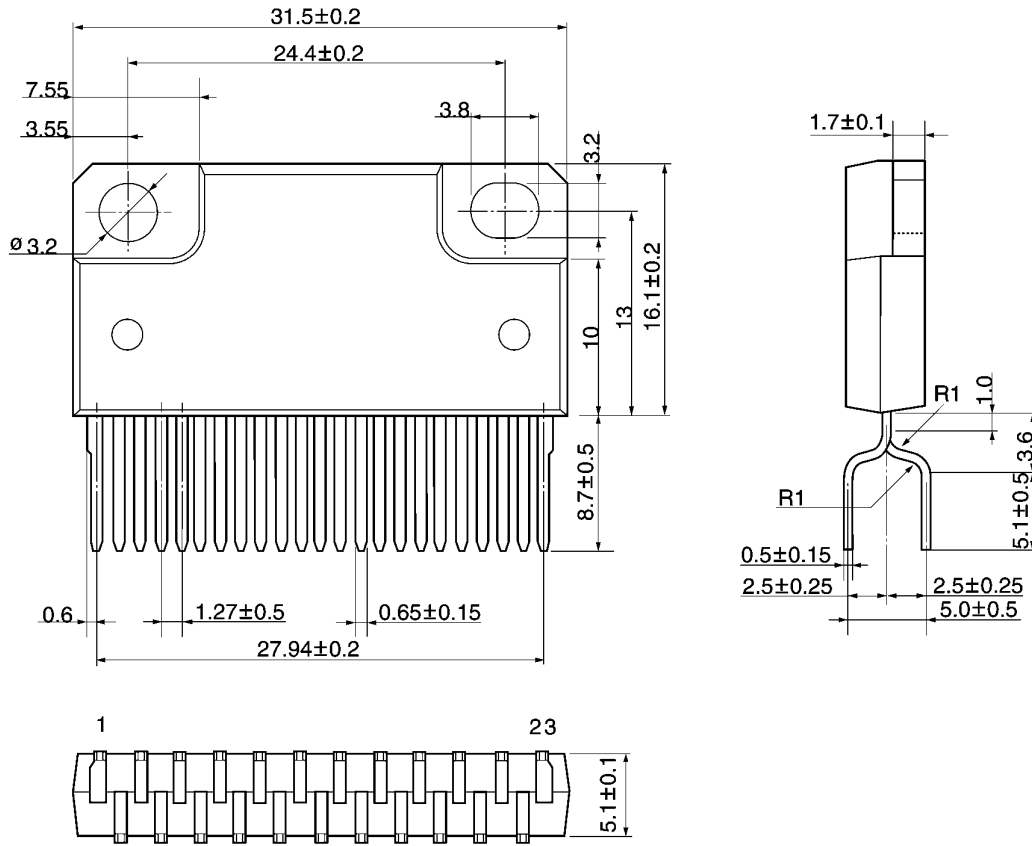


Weight: 6.1 g (typ.)

Package Dimensions

HZIP23-P-1.27H

Unit: mm



Weight: 6.1 g (typ.)

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